

### High-reliability discrete products and engineering services since 1977

## 2N3668-2N3670, 2N4103

#### SILICON CONTROLLED RECTFIERS

#### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### **MAXIMUM RATINGS**

Rating	Symbol	2N3668	2N3669	2N3670	2N4103	Units
Non-repetitive peak reverse voltage	V <sub>RM</sub>	150	330	660	700	V
Peak repetitive reverse voltage	V <sub>RRM</sub>	100	200	400	600	V
Peak forward blocking voltage	V <sub>FBOM</sub>	100	200	400	600	V
Forward current for case temperature $T_C$ = +80°C @ average DC value at a conduction angle of 180° RMS value	I <sub>FAV</sub>		1	8 2.5		А
Peak surge current for one cycle of applied voltage 60 Hz (sinusoidal), $T_C = 80^{\circ}C$ 50 Hz (sinusoidal), $T_C = 80^{\circ}C$	Іғм		2	200 200 170		А
Fusing current (T <sub>J</sub> = -40 to +100°C, t = 1 to 8.3ms)	l²t		1	170		A <sup>2</sup> s
Rate of change of forward current $V_{FB} = V_{BOO}$ , $I_{GT} = 200$ mA, 0.5ns rise time	di/dt		2	200		A/μs
Peak gate power for 10ns duration	P <sub>GM</sub>			40		W
Average gate power	P <sub>GAV</sub>		(	0.5		W
Storage temperature	T <sub>stg</sub>		-40 t	o +125		°C
Operating case temperature	T <sub>C</sub>		-40 t	o +100		°C

<sup>\*</sup>Any values of peak gate current or peak gate voltage to give the maximum gate power is permissible.

\* Temperature reference point is within 1/8" of the center of the underside of unit.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Characteristic	Symbol	2N3668		2N3669		2N3670			2N4103			Unite		
		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Units
Peak repetitive blocking voltage @ T <sub>c</sub> = 100°C	$V_{DROM}$	100	-	-	200	-	-	400	-	-	600	-	-	V
Forward peak blocking current $@T_C = 100^{\circ}C$ , $V_D = V_{DROM}$	I <sub>DOM</sub>	-	0.2	2	-	0.25	2.5	-	0.3	3	-	0.35	4	mA
Reverse peak blocking current @ $T_C = 100$ °C, $V_R = V_{RROM}$	I <sub>ROM</sub>	-	0.05	1	-	0.1	1.25	-	0.2	1.5	-	0.3	3	mA
Forward voltage drop @ 25A T <sub>C</sub> = 25°C	V <sub>F</sub>	-	1.5	1.8	-	1.5	1.8	-	1.5	1.8	-	1.5	1.8	V
DC gate-trigger current @ T <sub>C</sub> = 25°C	I <sub>GT</sub>	1	20	40	1	20	40	1	20	40	1	20	40	mA
DC gate-trigger voltage @ T <sub>C</sub> = 25°C	V <sub>GT</sub>	-	1.5	2	-	1.5	2	-	1.5	2	-	1.5	2	V
Holding current @ T <sub>C</sub> = 25°C	I <sub>H</sub>	0.5	25	50	0.5	25	50	0.5	25	50	0.5	25	50	mA
Critical rate of forward voltage $V_F = V_{BOO}$ , exponential rise $T_C = 100^{\circ}C$	dv/dt	10	100	-	10	100	-	10	100	-	10	100	-	V/µs



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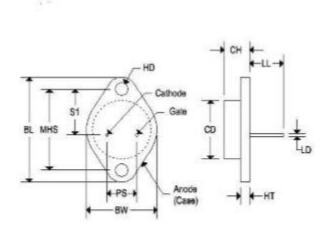
### SILICON CONTROLLED RECTFIERS

**ELECTRICAL CHARACTERISTICS** (@ maximum ratings and indicated case temperature (Tc)

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Characteristic	Symbol Mi	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Units
Turn-on time	t <sub>on</sub>	-	1.25	-	-	1.25	-	-	1.25	-	-	1.25	-	μs
(delay time + rise time)														
$V_D = V_{DROM}$ , $I_T = 8A$ , $I_G = 200$ mA, 0.1 $\mu$ s rise time, $T_C = 25$ °C														
Turn-off time	t <sub>off</sub>	-	20	50	-	20	50	-	20	50	-	20	50	μs
(reverse recovery time + gate recovery time)														
$I_F = 8A$ , 50ns pulse width, $dv_{FS}/dt = 20V/\mu s$ ,														
$di_r/dt = 30A/\mu s$ , $I_{GT} = 200mA$ , $T_C = 80^{\circ}C$														
Thermal resistance	R <sub>eJC</sub>	-	-	1.7	-	-	1.7	-	-	1.7	-	-	1.7	°C/W
Junction to case														

### MECHANICAL CHARACTERISTICS

Case:	TO-3
Marking:	Body painted, alpha-numeric
Pin out:	See below



	TO-3									
	Inc	hes	Millimeters							
	Min	Max	Min	Max 22.220						
CD	-	0.875								
CH	0.250	0.380	6.860	9.650						
HT	12	0.135	32	3.430						
BW	2 12	1.050	S - 10.7	26.670						
HD	0.131	0.188	3.330	4.780						
LD	0.038	0.043	0.970	1.090						
LL	0.312	0.500	7.920	12.700						
BL	1.550	) REF	39.37	0 REF						
MHS	1.177	1.197	29.900	30.400						
PS	0.420	0.440	10.670	11.180						
S1	0.655	0.675	16.640	17.150						



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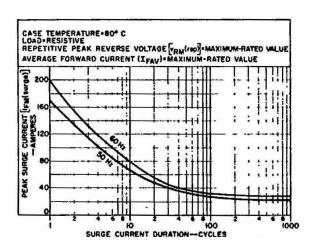


Fig. 1 - Peak surge current vs. surge current duration

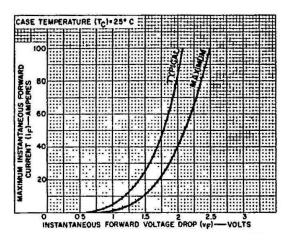


Fig. 2 - Instantaneous forward current vs. Instantaneous forward voltage drop



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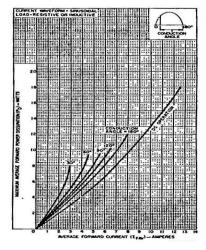


Fig. 3 — Power dissipation vs. forward current.

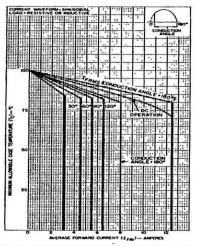


Fig. 4 — Maximum allowable case temperature vs. average forward current.

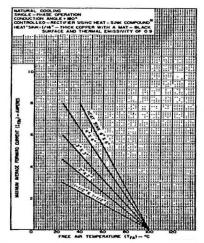


Fig. 5 — Natural-cooling operation guidance chart.

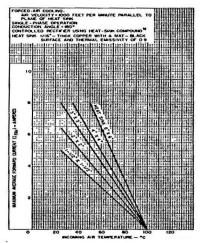


Fig. 6 — Forced-air cooling operation guidance chart.

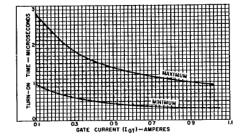


Fig. 7 — Turn-on time vs. gate current.